

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claim 1 (withdrawn): A semiconductor light emitting device comprising:
a substrate having a surface that has a difference-in-height portion;
a crystal growth layer formed on the surface of the substrate wherein at least a portion of the crystal growth layer is oriented along an inclined plane with respect to the surface of the substrate; and
a first conductive layer, an active layer and a second conductive layer formed on the crystal growth layer in a stacked arrangement and oriented along the inclined plane.

Claim 2 (withdrawn): The device of claim 1 wherein the substrate comprises a wurtzite compound.

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Claim 3 (withdrawn): The device of claim 1 wherein the wurtzite compound forms a layer oriented along a principal plane of the substrate and wherein the inclined plane is inclined with respect to the principal plane.

Claim 4 (withdrawn): The device of claim 1 wherein the inclined plane comprises at least one of a S-plane and a {11-22} plane.

Claim 5 (withdrawn): The device of claim 1 wherein the difference-in-height portion comprises a shape selected from the group consisting of a stripe shape, a rectangular shape, a round shape, a triangular shape, a hexagonal shape and combinations thereof.

Claim 6 (withdrawn): The device of claim 1 wherein the crystal growth layer comprises a shape selected from the group consisting of a stripe shape, a rectangular shape, a round shape, a triangular shape, a hexagonal shape and combinations thereof.

Claim 7 (withdrawn): The device of claim 1 wherein the crystal growth layer further comprises a portion which is substantially parallel with respect to a principal plane along which at least a portion of the substrate is oriented.

Claim 8 (withdrawn): The device of claim 1 wherein the semiconductor light emitting device comprises a light emitting diode structure.

Claim 9 (withdrawn): The device of claim 1 wherein the semiconductor light emitting device comprises a semiconductor laser structure.

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Claim 10 (withdrawn): The device of claim 1 wherein the surface of the substrate is oriented along a C-plane such that an end portion of the different-in-height portion is oriented perpendicular with respect to at least one of a $\langle 1-100 \rangle$ direction and a $\langle 11-20 \rangle$ direction and wherein the growth of the crystal growth layer depends on a shape of the difference-in-height portion.

Claim 11 (withdrawn): The device of claim 1 wherein at least a portion of the crystal growth layer forms a valley having a cross-section that is substantially V-shaped.

Claim 12 (withdrawn): The device of claim 11, wherein an electrode is formed on the substantially V-shaped valley.

Claim 13 (withdrawn): A device of claim 1, wherein said crystal growth layer has a plurality of crystal growth layer portions perpendicularly formed within a plane being approximately parallel to a principal plane of the substrate.

Claim 14 (withdrawn): The device of claim 1, wherein the crystal growth layer comprises a GaN semiconductor.

Claim 15 (withdrawn): The device of claim 1, wherein the crystal growth layer is grown at a temperature of about 1100°C or less.

Claim 16 (withdrawn): The device of claim 1, wherein the crystal growth layer is grown at pressure of about 100 Torr or more.

Claim 17 (withdrawn): A semiconductor light emitting device comprising:
a substrate comprising a substrate layer composed of a wurtzite compound formed along a principal plane of the substrate wherein the layer includes a different-in-height portion formed in a surface of the substrate layer;

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a crystal growth layer formed on the surface of the substrate layer wherein at least a portion of the crystal growth layer is oriented along an inclined plane that is inclined with respect to the principal plane;

a first conductive cladding layer, an active layer and a second conductive layer formed on the crystal growth layer in a sequentially stacked arrangement oriented along two or more planes of the crystal growth layer including the inclined plane such that one or more light emission regions are formed; and

one or more electrodes separately formed in the light emission regions.

Claim 18 (withdrawn): The device of claim 17, wherein the inclined plane comprises at least one of an S-plane and a {11-22} plane.

Claim 19 (withdrawn): The device of claim 17, wherein the principal plane comprises at least one of a C-plane and a {0001} plane.

Claim 20 (withdrawn): The device of claim 17, wherein wavelengths of two or more kinds of light emitted from the light emission regions are different from each other.

Claim 21 (withdrawn): The device of claim 20, wherein at least one of a composition and a thickness of the active layer varies with respect to the light emission regions such that the wavelengths are different from each other.

Claim 22 (withdrawn): The device of claim 17, wherein the light emitting device has a light emitting diode structure allowing simultaneous emission of light associated with two or more colors.

Claim 23 (withdrawn): The device of claim 17, wherein the light emitting device has a semiconductor laser structure allowing simultaneous emission of light of two or more colors.

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Claim 24 (withdrawn): The device of claim 17, wherein the substrate layer is oriented along a C-plane such that an end portion of the different-in-height portion is perpendicularly directed with respect to at least one of a $\langle 1-100 \rangle$ direction and a $\langle 11-20 \rangle$ direction and wherein the growth of the crystal growth layer depends on a shape of the different-in-height portion.

Claim 25 (withdrawn): The device of claim 17, wherein at least a portion of the crystal growth layer forms a valley having a cross-section that is approximately V-shaped.

Claim 26 (withdrawn): The device of claim 25, wherein at least one of the electrodes is formed on the approximately V-shaped valley.

Claim 27 (withdrawn): The device of claim 17, wherein the crystal growth layer comprises a GaN semiconductor.

Claim 28 (withdrawn): The device of claim 17, wherein the crystal growth layer is grown at a temperature of about 1100°C or less.

Claim 29 (withdrawn): The device of claim 17, wherein the crystal growth layer is grown at a pressure of about 100 Torr or more.

Claim 30 (currently amended): A method of fabricating a semiconductor light emitting device, comprising the steps of:

forming a wurtzite-type compound semiconductor layer on a substrate oriented along a principal plane such that a difference-in-height portion is formed in a surface of the wurtzite-type compound semiconductor;

forming a crystal growth layer at least a portion of which is oriented along an inclined plane inclined with respect to the principal plane by crystal growth on the surface; ~~and~~

applying a first conductive cladding layer, an active layer, and a second conductive layer in a stacked arrangement along a region extending in parallel to said inclined plane;

forming a first mask material layer, forming a first window region in the first mask material layer, and forming a first electrode layer through the first window region; and

forming a second mask material layer, forming a second window region in the second mask material layer at a position different from that of the first window region, and forming a second electrode layer through the second window region;

wherein one or more light emission regions having different characteristics are formed by using the first electrode layer and the second electrode layer.

Claim 31 (canceled)

Claim 32 (original): The method of claim 30, wherein the semiconductor light emitting device is separated into a plurality of light emission regions electrically independent from each other.

Claim 33 (original): The method claim 32, wherein an amount of current injected in the light emission regions is capable of being adjusted to establish wavelengths of light emitted from the light emission regions to a desired value.

Claim 34 (original): The method of claim 30 comprising the steps subsequent to the applying step of:

forming a resist layer, and forming a specific pattern of an electrode layer by a lift-off process.

Claim 35 (original): The method of claim 30 comprising the steps subsequent to the applying step of:

forming a resist layer having a window region, forming an electrode layer to cover said resist layer including an inner region of said window region, and removing said resist layer together with said electrode layer excluding an electrode portion formed on a bottom region of the window region by a lift off process.

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Claim 36 (original): The method of claim 30, wherein the crystal growth layer is grown at a temperature of about 1100°C or less.

Claim 37 (original): The method of claim 30, wherein the crystal growth layer is grown at a pressure of about 100 Torr or more.

Claim 38 (new): A method of producing a semiconductor light emitting device, the method comprising the steps of:

forming a wurtzite compound layer having a surface that has a difference-in-height portion;

forming a crystal growth layer on the surface of the wurtzite compound layer wherein at least a portion of the crystal growth layer is oriented along an inclined plane selected from the group consisting of an S-plane, a {11-22} plane and planes substantially equivalent thereto; and

forming a first conductive layer, an active layer and a second conductive layer in a sequential manner on the crystal growth layer such that the first conductive layer, the active layer and the second conductive layer are oriented along the inclined plane.

Claim 39 (new): The method of claim 38, wherein the semiconductor light emitting device is separated into a plurality of light emission regions electrically independent from each other.

Claim 40 (new): The method claim 39, wherein an amount of current injected in the light emission regions is capable of being adjusted to establish wavelengths of light emitted from the light emission regions to a desired value.

Claim 41 (new): The method of claim 38 further comprising the steps of:
forming a resist layer, and forming a specific pattern of an electrode layer by a lift-off process.

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Claim 42 (new): The method of claim 38 further comprising the steps of:
forming a resist layer having a window region, forming an electrode layer to cover said resist layer including an inner region of said window region, and removing said resist layer together with said electrode layer excluding an electrode portion formed on a bottom region of the window region by a lift off process.

Claim 43 (new): The method of claim 38, wherein the crystal growth layer is grown at a temperature of about 1100°C or less.

Claim 44 (new): The method of claim 38, wherein the crystal growth layer is grown at a pressure of about 100 Torr or more.
